

| L Number | Hits | Search Text | DB | Time stamp |
|-------------|------|---|---|---------------------|
| - | 140 | (aluminum or al) same (N or nitrogen) near4 (deposit\$4 or growth) and 117\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 15:32 |
| - | 10 | (aluminum or al) near10 (promot\$4 or enhanc\$4 or improv\$5) same (N or nitrogen) near4 (deposit\$4 or growth) and 117\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 15:29 |
| - | 66 | ((aluminum or al) same (N or nitrogen) near4 (deposit\$4 or growth) and 117\$4.ccls.) and (MBE or molecular adj beam adj epitax\$) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 15:36 |
| - | 45 | (N or nitrogen) near3 dop\$4 same (aluminum or al) near4 layer and 117\$5.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 16:00 |
| - | 53 | (nitrogen) near3 dop\$4 same (aluminum or al) and 117\$5.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 16:02 |
| - | 33 | (nitrogen) near3 dop\$4 same (aluminum or al) and 117/84-109.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 16:04 |
| - | 14 | (nitrogen) near3 dop\$4 same (aluminum) and 117/84-109.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 16:07 |
| - | 5 | (nitrogen) near3 dop\$4 same "iii-v" and 117/84-109.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 16:07 |
| - | 39 | "iii-v" same (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 11:29 |
| - | 4 | "iii-v" same (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) same monolayer and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 11:33 |
| - | 2 | ((algap or algan) same (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4)) and 117/\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 11:34 |
| - | 17 | (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4).ti. and 117\$5.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 11:45 |
| - | 11 | 117\$5.ccls. and monolayer near6 deposit\$4 same (gallium or ga! and aluminum and nitrogen) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 11:45 |

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| - | 36 | (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) and 117\$5.ccls. and quantum near4 well | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 11:51 |
| - | 24 | ((ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) and 117\$5.ccls. and quantum near4 well) and "iii-v" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 11:46 |
| - | 3 | (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) same (algainp) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 13:08 |
| - | 6 | (ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4) or sequent\$4 near4 deposit\$4) and nitrogen near4 dop\$4 and 117\$5.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 13:12 |
| - | 4 | algainnas same quantum | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 15:54 |
| - | 9 | algainnas | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 15:57 |
| - | 10 | (algaasn or algan or gaaln or gaalasn) same (gainas or gaasin) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 16:02 |
| - | 25 | "In-based" near5 "III-V" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 16:04 |
| - | 1 | gainp same algainp same (hetero or hetero\$1structure) same nitrogen | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 16:07 |
| - | 54 | less near4 (atom\$3 near3 layer or monolayer) and 117\$4.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 16:16 |
| - | 16 | less near4 (atom\$3 near3 layer or monolayer) and 117\$4.ccls. and "iii-v" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 16:28 |
| - | 4 | Mbe same (algan or gaaln) and 117\$5.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 16:29 |
| - | 94 | "iii-v" same (indium same aluminum same nitrogen or nitride) same ternary | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 16:47 |
| - | 6 | "iii-v" same ternary same nitrogen near4 dop\$4 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 16:48 |

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| - | 65 | "iii-v" same nitrogen near4 dop\$4 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/11 17:19 |
| - | 115 | (AlGa _N or gallium near2 aluminum near3 nitride) same (gallium near3 indium) same (active or cladding) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 09:43 |
| - | 17 | (AlGa _N or gallium near2 aluminum near3 nitride) same (gallium near3 indium) same well same thickness | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 09:47 |
| - | 11 | (AlGa _N or gallium near2 aluminum near3 nitride) same (gallium near3 indium) same monolayer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 09:49 |
| - | 23 | (AlGa _N or gallium near2 aluminum near3 nitride) same monolayer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 10:04 |
| - | 1 | (AlGa _N or gallium adj aluminum adj nitride or GaAl _N or gallium adj aluminum adj nitride) same (Gaal _N or alga _N) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 10:38 |
| - | 126 | aluminum near4 gallium same mask\$3 and 257/\$5.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 10:44 |
| - | 49 | quantum near3 wire same "iii-v" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 11:02 |
| - | 46 | diffraction near4 grating same "iii-v" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 11:06 |
| - | 9 | alga _N nas | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 11:35 |
| - | 5 | (ingaas or gainas) same (algaasn or gaalasn) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 11:41 |
| - | 2 | pseudo\$lmixed near4 crystal | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 11:39 |
| - | 10 | (ingaas or gainas) same monolayer and 117\$5.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 11:42 |
| - | 113 | (ingaas or gainas) near4 superlattice | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 11:49 |

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| - | 2 | (ingaas or gainas) near4 superlattice same aluminum | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 11:49 |
| - | 2 | ternary near4 superlattice same aluminum | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 13:23 |
| - | 15 | superlattice same "iii-v" same monolayer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 13:39 |
| - | 23 | superlattice same "iii-v" same nitride | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 13:45 |
| - | 6 | superlattice same "iii-v" same (aluminum and indium) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 13:55 |
| - | 11 | superlattice same "iii-v" same nitrogen | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 13:55 |
| - | 1 | (aluminum near3 nitride or aln) same (indium near3 phosphide or inp) same superlattice | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 16:08 |
| - | 2 | (aluminum near3 nitride or al\$2n) same (indium near3 phosphide or in\$2p) same superlattice | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 16:09 |
| - | 2 | (aluminum near3 nitride or \$2al\$2n) same (indium near3 phosphide or \$2in\$2p) same superlattice | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 16:11 |
| - | 14 | (aluminum near3 nitride or al\$2n) same (indium near3 phosphide or inp) same monolayer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 16:15 |
| - | 98 | (MBE or molecular adj beam adj epitax\$4 or CBE) same solid near4 source and "iii-v" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 17:02 |
| - | 42 | compound near2 semiconductor same "iii-v" same nitrogen near3 dop\$4 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 17:04 |
| - | 1 | compound near2 semiconductor same "iii-v" same nitrogen near3 dop\$4 same superlattice | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 17:10 |
| - | 3 | "iii-v" same nitrogen near3 dop\$4 same superlattice | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 17:11 |

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| - | 7 | superlattice same (indium and aluminum and nitrogen) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 17:29 |
| - | 7 | nitrogen near3 dop\$4 same "iii-v" same aluminum | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/12 17:31 |
| - | 31 | nitrogen near3 dop\$4 same aluminum near3 gallium | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/13 13:47 |
| - | 21 | algainp same mask\$4 same dop\$4 | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/13 17:08 |